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CLAIMS

1. A high frequency dielectric ceramics composition constituted by combining (Zn_{1,x}M_x)TiO₃ and yTiO₂ satisfies the conditions of:

wherein M is Mg, Co or Ni,

'x' is $0 \le x \le 0.6$ in case of Mg and 'x' is $0 \le x \le 1$ in case of Co, and $0 \le x \le 1$ in case of Ni, and

0≤y≤0.8.

2. A high frequency dielectric ceramics composition preparation method in which material powder of ZnO, MO (in this respect, MO is MgO, CoO or NiO) and TiO₂ is weighed according to a composition range of (Zn₁-xM₂)TiO₃ and yTiO₂ (M is one of Mg, Co and Ni, x is 0≤x≤0.6 in case of Mg, x is 0≤x≤1 in case of Co, x is 0≤x≤1 in case of Ni, and y is 0≤y≤0.8), mixed and dried,

calcined at a temperature of 850~950°C,

the calcined powder is crushed,

the crushed power is shaped,

the shaped body is fired at a temperature of 925~1100°C, and

 $(Zn_{1-x}M_x)TiO_3$ is calcined at a temperature corresponding to a region (region II) of below a phase dissociation temperature as shown in Figure 2 to obtain $(Zn_{1-x}M_x)TiO_3$ (M is Mg, Co or Ni) of a single phase of rhombohedral/hexagonal crystal.

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- 3. The method of claim 2, wherein the shaped body is made in a manner that an aqueous solution adding a PVA binder is sprayed onto the crushed powder to make a granule, to which a pressure is applied.
- The method of claim 3, further comprises a step for maintaining the shaped body at a temperature of 300-500°C for a predetermined time and removing the binder.
- The method of claim 2, wherein (Zn₁-xMx)TiO₃ is first calcined and
 yTiO₂ (0≤y≤0.8) is added to (Zn₁-xMx)TiO₃ and then sintered.
 - 6. The method of claim 2, wherein $(Zn_{1-x}M_x)TiO_3$ and $yTiO_2$ are sintered at the same time and sintered.
- 7. The method of claim 2, wherein TiO2 is anatase or rutile.
 - 8. A high frequency dielectric ceramics composition constituted from combination of $(Zn_{1-a}Mg_{1-b}Co_{1-c}Ni_{1-d})TiO_3$ and $yTiO_2$ $(0 \le a \le 1, 0 \le b \le 1, 0 \le c \le 1, 0 \le d \le 1)$, and $0 \le y \le 0.8$.

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9. Various high frequency devices such as a stacked chip capacitor, a stacked chip filter, a stacked chip capacitor/inductor composite device and a module, a low-temperatur sintered substrate, a resonator and a filter or a

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ceramic ant nna, are fabricated by using the dielectric composition of claim 1.